

Power Transistors

Panasonic**2SC3979, 2SC3979A**

Silicon NPN triple diffusion planar type

For high breakdown voltage high-speed switching

■ Features

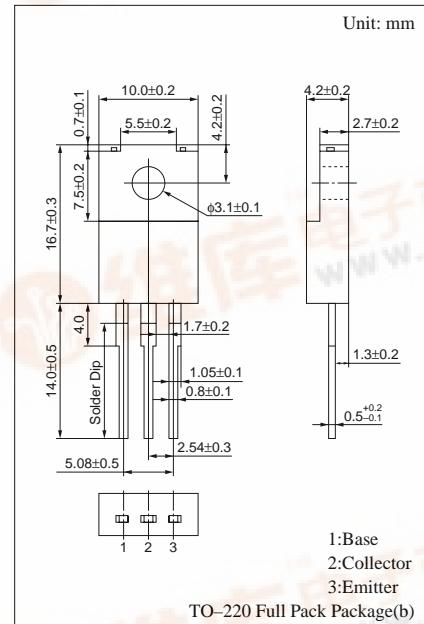
- High-speed switching
- High collector to base voltage V_{CBO}
- Wide area of safe operation (ASO)
- Satisfactory linearity of forward current transfer ratio h_{FE}
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

| Parameter | Symbol | Ratings | Unit |
|---|-----------|-------------|------------------|
| Collector to base voltage 2SC3979 | V_{CBO} | 900 | V |
| 2SC3979A | | 1000 | |
| Collector to emitter voltage 2SC3979 | V_{CES} | 900 | V |
| 2SC3979A | | 1000 | |
| Collector to emitter voltage | V_{CEO} | 800 | V |
| Emitter to base voltage | V_{EBO} | 7 | V |
| Peak collector current | I_{CP} | 5 | A |
| Collector current | I_C | 3 | A |
| Base current | I_B | 1 | A |
| Collector power dissipation | P_C | 40 | W |
| $T_C=25^\circ\text{C}$ | | 2 | |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

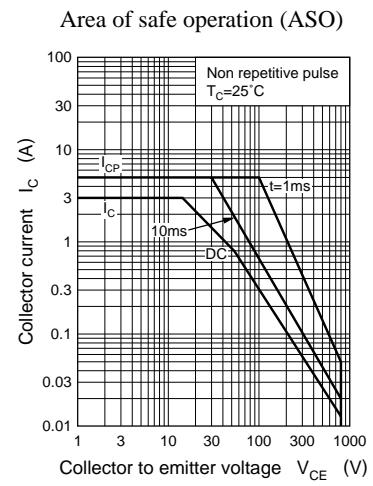
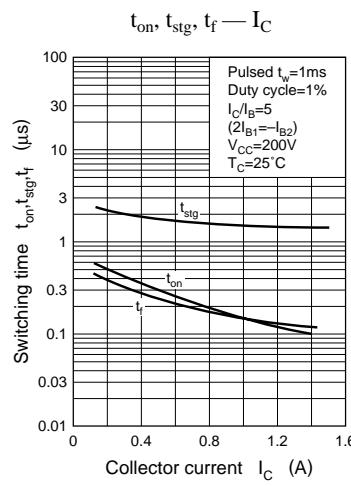
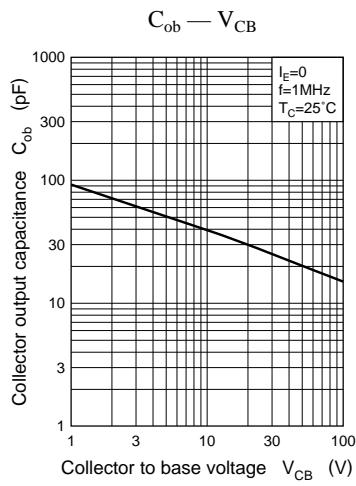
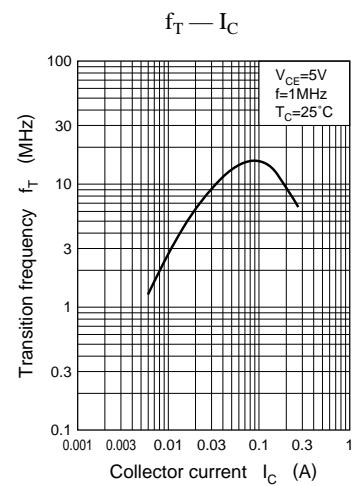
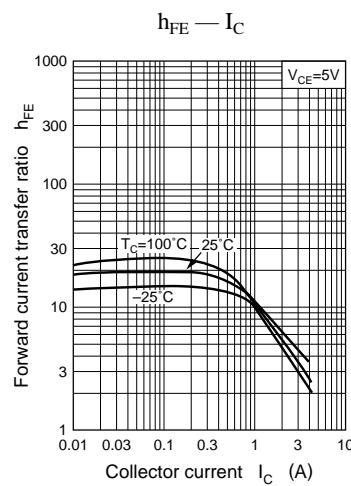
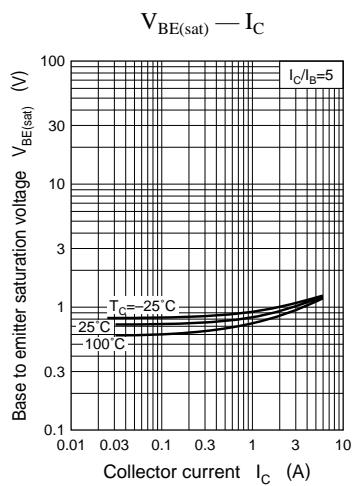
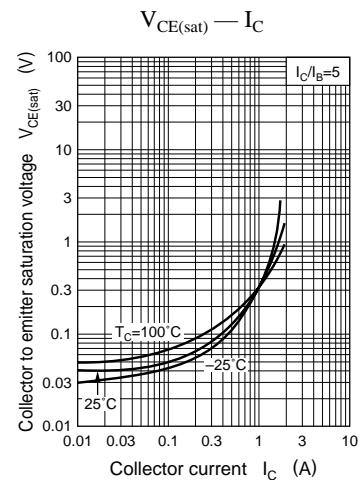
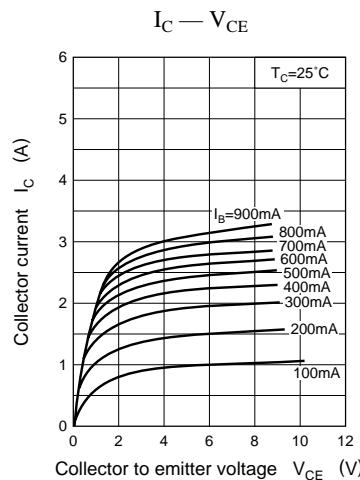
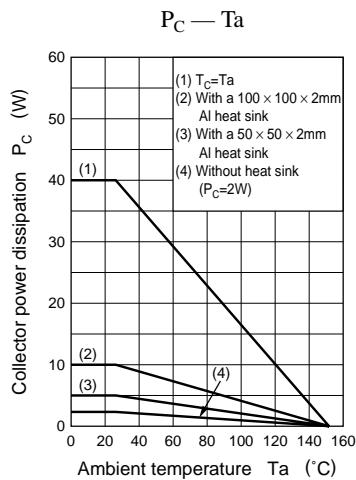
■ Electrical Characteristics ($T_C=25^\circ\text{C}$)

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|----------------------|--|-----|-----|-----|---------------|
| Collector cutoff current 2SC3979 | I_{CBO} | $V_{CB} = 900\text{V}, I_E = 0$ | | | 50 | μA |
| 2SC3979A | | $V_{CB} = 1000\text{V}, I_E = 0$ | | | 50 | |
| Emitter cutoff current | I_{EBO} | $V_{EB} = 7\text{V}, I_C = 0$ | | | 50 | μA |
| Collector to emitter voltage | V_{CEO} | $I_C = 10\text{mA}, I_B = 0$ | 800 | | | V |
| Forward current transfer ratio | h_{FE1} | $V_{CE} = 5\text{V}, I_C = 0.1\text{A}$ | 8 | | | |
| | h_{FE2} | $V_{CE} = 5\text{V}, I_C = 0.8\text{A}$ | 6 | | | |
| Collector to emitter saturation voltage | $V_{CE(\text{sat})}$ | $I_C = 0.8\text{A}, I_B = 0.16\text{A}$ | | | 1.5 | V |
| Base to emitter saturation voltage | $V_{BE(\text{sat})}$ | $I_C = 0.8\text{A}, I_B = 0.16\text{A}$ | | | 1.5 | V |
| Transition frequency | f_T | $V_{CE} = 5\text{V}, I_C = 0.15\text{A}, f = 1\text{MHz}$ | 10 | | | MHz |
| Turn-on time | t_{on} | $I_C = 0.8\text{A}, I_{B1} = 0.16\text{A}, I_{B2} = -0.32\text{A}, V_{CC} = 250\text{V}$ | | | 0.7 | μs |
| Storage time | t_{stg} | | | | 2.5 | μs |
| Fall time | t_f | | | | 0.3 | μs |



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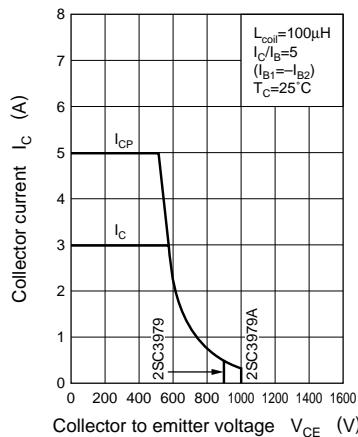
2SC3979, 2SC3979A



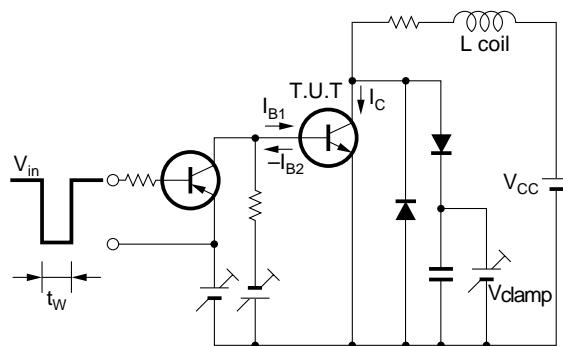
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Area of safe operation, reverse bias ASO



Reverse bias ASO measuring circuit



$R_{th(t)} — t$

